

# Quantum Information and Solid State Systems

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Enabling developments for defect-based quantum information





Optical image of single defects in commercial diamond substrate<sup>1</sup>.

## (Not just in diamond!) UNIVERSITY of WASHINGTON

### Single defect experiments Measurement-based quantum entanglement



Distributed model of quantum information processing<sup>2</sup>

<sup>1</sup>Edmonds *et al.* (Warwick, UW, HP) *PRB* 86, 035201 (2012) <sup>2</sup>Nickerson, Fitzsimons, Benjamin PRX 4 041041 (2014)

## Removing the need for local interaction



Looks like a local interaction that needs high level of control







(Significant portion of my research)

This edge is created when a c-phase gate is applied to the following input states.



(Output state is local unitary equivalent to a Bell state.)



Can be created by measurement of emitted photons!



- -
	-
	-
- $\begin{array}{|c|l|} \hline \textbf{O} \left[\left|0\right\rangle \otimes \left|0\right\rangle\right] \left| \mathrm{vac} \right\rangle \\[1mm] \hline \hline \textbf{2} \left[\left(\left|0\right\rangle + \left|1\right\rangle\right) \otimes \left(\left|0\right\rangle + \left|1\right\rangle\right)\right] \left| \mathrm{vac} \right\rangle \\[1mm] \hline \textbf{3} \left[\left(\left|e\right\rangle + \left|1\right\rangle\right) \otimes \left(\left|e\right\rangle + \left|1\right\rangle\right)\right] \left| \mathrm{vac} \right\rangle \\[1mm] \h$

 $\boxed{\textbf{5}\Big[ ( \vert 01 \rangle + i \vert 10 \rangle ) b_{\text{L}}^{\dagger} + (i \vert 01 \rangle + \vert 10 \rangle ) b_{\text{R}}^{\dagger} \Big] \, \vert \text{vac} \rangle }$  $\bigodot (|01\rangle + i|10\rangle)$ 

## System requirements (subset)



- > Two atoms must emit identical photons
- > Photon must be detected
	- Described protocol scales linearly with detection efficiency
	- Protocols robust to loss error scale as square of efficiency
- > At least 2 qubits per node with local operations
- > Entanglement rate should be significantly faster than decoherence time.

# Many different defect systems

### > **Diamond: NV**<sup>-</sup>, SiV<sup>-</sup>, SiV<sup>0</sup>

- Room temperature second-long spin coherence time
- Phonon assisted optical transitions
- $>$  SiC:  $V_{si}$ - $V_{ci}$ ,  $V_{si}$ 
	- Mature host crystal for device fabrication
	- Phonon assisted optical transitions
- > Si: P, Su
	- Silicon!!!
	- Nonradiative recombination
- > Rare-earth doped crystals:  $Tm^{3+}$ ,  $Pr^{3+}$ ,  $Er^{3+}$  in KTP, YSO, YAG, etc.
	- 6-hour quantum memory
	- Weak optical transitions

## > Quantum dots

- Advanced device integration, large oscillator strength
- Short decoherence time (single microseconds)

## > **ZnO: Ga, In, Al**

- high optical homogeneity
- near-UV optical transitions

# Many different defect systems

### > **Diamond: NV**<sup>-</sup>, SiV<sup>-</sup>, SiV<sup>0</sup>

– Room temperature second-long spin coherence time

– Phonon assisted optical transitions

### $\overline{\phantom{a}}$  (*Mature host crystal for device fabrication*) Outstanding issues:

– Phonon assisted optical transitions of the contract of the contract of the contract of the contract of the c<br>The contract of the contract o  $\blacksquare$  Nonradiative recombination deterministic defect creation LARGE PARAMETER SPACE long characterization time lack of predictive modeling

> R degradation of quantum properties with device integration

– Advanced device integration, large oscillator strength

– Short decoherence time (single microseconds)

## > **ZnO: Ga, In, Al**

 $>$  Quantum dots and dots are  $\sim$ 

 $>$  Si $\sim$ 

– Silicon!!!

 $>$  Si  $\sim$  P,  $\sim$ 

– high optical homogeneity

– 6-hour quantum memory

– Weak optical transitions

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## Realization of measurement-based entanglement using NV centers in diamond



Entanglement Fidelity: 0.87

Coherence time: 1s

Entanglement attempt rate: 100 kHz

Entanglement rate: 4 mHz

Success probability:  $<$  1e-7

## Reasons for poor entanglement efficiency: 1) Phonon assisted radiative recombination



Reasons for poor entanglement efficiency: 2) Difficult to collect the emitted photon







## Solution: use a cavity to enhance NV emission into a useful spectral and spatial mode



Mirror 1 Mirror 2

$$
F_{\text{cav}} = \frac{3}{4\pi^2} \left(\frac{\lambda}{n_{\text{cav}}}\right)^3 \frac{n_{\text{cav}}}{n_D} \frac{Q}{V_{\text{mode}}} \frac{|E_{\text{NV}}|^2}{|E_{\text{max}}|^2} \frac{\overrightarrow{E}_{\text{NV}} \cdot \overrightarrow{\mu}}{|E_{\text{NV}}||\overrightarrow{\mu}|}
$$

Santori, Faraon, Fu, Barclay (HP Labs)

Lukin/Loncar/Hu (Harvard) 

Englund (MIT)

Wang (U. Oregon)

Childress (McGill) 

Hanson (Delft)

…

- Cavity is on resonance with NV
- NV is at cavity maximum
- NV electric dipole is aligned to cavity mode.
- **High quality factor**
- Small mode volume

And do it all on a chip for scalability (with the NV center in diamond for now...)

 $20 \mu m$ 

 $A \rightarrow B$ 

 $\mathbf{B}$ 

6

 $\left|e\right\rangle$ 

 $\frac{\pi}{2}$ 

 $\mathcal{A}^{\mathcal{P}}$ 

 $|0\rangle$ 

 $|1\rangle$ 

 $\overline{6}$ 

 $-2-0$ 

 $|0\rangle$ 

 $|e\rangle$ 

 $\frac{\pi}{2}$ 

 $|1\rangle$ 

# Schematic for two-NV entanglement



- 1) Can we implement all passive components?
- 2) Can we efficiently extract photons from the NV center?
- 3) Can we stabilize the NV center optical transition?
- 4) Can we efficiently detect the photons?

# Passive Photonics



Gould *et al.* (UW) JOSA B 33, B35 (2016)

Take away message: performance and fabrication tolerances are reasonable for simple circuits.

# Resonant enhancement of the zero-phonon-line emission from a single NV center



Gould, Schmidgall, Dadgostar, Hatami, Fu, "Efficient extraction of zerophonon-line photons from single nitrogen-vacancy centers in an integrated GaP-on-diamond platform," Physical Review Applied (2016)

# Zero Phonon Line Collection





# Single Photon Source



# My groups current efforts in diamond



- 1) Moving detectors on-chip
- 2) Tuning and stabilizing the optical transition frequency of near-surface NV centers

## Current efforts in diamond



- 1) Moving detectors on-chip
- 2) Stabilizing the optical transition frequency of near-surface NV centers

## Current efforts in diamond

PLE Scans For 242 NVs



1) Moving detectors on-chip

2) Tuning and stabilizing the optical transition frequency of near-surface NV centers UNIVERSITY of WASHINGTON

## Example of quantum defect "discovery": donors in ZnO

## Donors in 4 direct-band gap semiconductors



Energy (eV)

1.59 Energy (eV)

## Gallium donor in ZnO: longitudinal spin relaxation time



Theoretical work still in progress for wurtzite crystal structure. 

## Double pulse experiment



## Inhomogeneous dephasing time



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(Spin-echo measurement under construction.)

## Triple pulse experiment (spin-echo)





T2 data In a commercial, high-purity substrate- no "engineering"

$$
T2 = 26.7 \pm 7.9 \,\mu s
$$



# Summary and outlook

- > Measurement-based model of quantum computing has several attractive features
	- Qubits do not need directly interact
	- Network is created by photons
- > Utilizing defects for the nodes is promising but progress is slow



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could also allow multifunctional sensing. However, the synthesis of isotope free quantum grade novel host materials, identification and incorporation of unique color centers, characterization of their quantum properties (coherence times, spectral stability etc.) and the understanding of their interactions with the external excitations (optical, electrical etc.) still remain significant challenges/unknowns.



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